Propagation behaviors of thickness–twist modes in an inhomogeneous piezoelectric plate with two imperfectly bonded interfaces

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1. Introduction

Piezoelectric materials can be made into various functional devices, such as sensors, actuators, filters and delay lines, which are widely used in electronic technology, mechanical engineering, medical appliance and other modern industrial fields [1]. Owing to wide application, the mechanism study of propagation of waves in piezoelectric structures and devices has drawn increasing attention of researchers in recent years [2–4]. Thickness–twist vibration modes (anti-plane or shear horizontal modes) of crystal plates are often used as the operating modes for resonators and acoustic wave sensors [5,6]. When the sixfold axis of a 6 mm crystal is parallel to the major surface of a plate, thickness–twist waves can propagate not only in a homogeneous piezoelectric plate [7,8], but in an inhomogeneous piezoelectric plate as well [9–11].

In principle, the mechanical and the electrical behaviors in piezoelectric materials should satisfy the kinetic equations and Maxwell equations. Along this approach, the shear horizontal waves in two inhomogeneous media [12,13] and in functionally graded piezoelectric layered structures [14,15] have been respectively investigated. Meanwhile, due to the brittleness nature of piezoelectric ceramics and the possible defects of impurity, cavities and micro-cracks, failures of devices take place easily under mechanical and/or electrical loadings. In order to overcome above-mentioned disadvantages, the shear horizontal waves in a pre-stressed layered piezoelectric structure have been considered [16–18]. Besides, SAW devices loaded with viscous liquid have also been taken into account [19,20].

However, most of the work is on the perfectly bonding interface between the two portions, i.e. the displacement and the tractions are continuous [12–20]. It has been recently pointed out that imperfectly bonding sometimes exists in devices and little is known about its effects [21], e.g., the aging of the glue which is applied at an interface, the defection of fabrication and corrosion of the materials, etc. In the simplest description of the mechanical behavior of an imperfect interface, the interface can be treated as a layer that geometrically has a zero thickness but still possesses elasticity and interface elastic strain energy, e.g., the shear-lag model in which the tangential displacement at an interface is allowed to be different from both sides of the interface in order to accounting for the deformation of the interface layer [22–25].

In this paper, we investigate the effect of the imperfectly bonded interfaces in an inhomogeneous piezoelectric plate in which the central portion is different from the rest portions using a spring-type relation [26], which is different from the shear-lag model [22–25]. Different from the previous work, the mechanical imperfection and the electrical imperfection are all taken into account. Since the material tensors of crystals of 6 mm symmetry have the same structures as polarized ceramics, our analysis is also valid for 6 mm piezoelectric crystals. This includes widely used materials like ZnO and AlN.

2. Governing equations and boundary conditions

Consider an inhomogeneous piezoelectric plate of 6 mm crystals or polarized ceramics with the depth of 2h, as shown in Fig. 1. The ceramic material is poled in the x3 direction determined...
by the right-hand rule from the $x_1$ and $x_2$ axes. The central portion $x_1 < |a|$ is made of one piezoelectric material, and the outer portions $x_1 > |a|$ are made of another one. We consider the imperfect boundary conditions at $x_1 = |a|$. The plate is unelectroded, and the surfaces are traction-free at $x_2 = \pm h$.

### 2.1. The governing equations

The thickness–twist mode of the central portion ($x_1 < |a|$) can be represented by displacement components $u$ and electrical potential function $\varphi$ as follows:

$$
\begin{align*}
\mathbf{u}_1 &= 0, \quad u_2 = 0, \quad u_3 = u(x_1, x_2, t), \quad \varphi = \varphi(x_1, x_2, t)
\end{align*}
$$

A function $\psi$ can be introduced through $\varphi = \psi + eu/c$ [9–11], and the governing equations of thickness–twist mode can be obtained:

$$
\begin{align*}
\mathbf{e} \nabla^2 u &= \rho \mathbf{u}, \quad \nabla^2 \psi = 0 \\
\text{where} \quad \nabla^2 &= \partial^2 / \partial x_i^2 + \partial^2 / \partial x_j^2 \text{ is the Laplace operator, } \rho \text{ is the mass density}, \quad \varepsilon_{44} = \varepsilon, \quad \varepsilon_{52} = \varepsilon \text{ and } \varepsilon_{11} = \varepsilon \text{ are the elastic, the piezoelectric and the permittivity coefficients, respectively. The relative electric constant is } \varepsilon = \varepsilon_c + \varepsilon_{c}^2/\varepsilon. \text{ The nontrivial stress and electric displacement components are:}
\end{align*}
$$

$$
\begin{align*}
T_{23} &= cu_{2} + e \psi_{2}, \quad T_{13} = cu_{1} + e \psi_{1} \\
D_{2} &= -e \psi_{2}, \quad D_{1} = -e \psi_{1}
\end{align*}
$$

where an index after a comma denotes partial differentiation with respect to the coordinate.

Similarly, for the outer regions ($x_1 > |a|$) of the plate, the governing equations are:

$$
\begin{align*}
\mathbf{e} \nabla^2 u &= \rho \mathbf{u}, \quad \nabla^2 \psi = 0
\end{align*}
$$

The nontrivial stress and electric displacement components are:

$$
\begin{align*}
T'_{23} &= cu'_{2} + e \psi'_{2}, \quad T'_{13} = cu'_{1} + e \psi'_{1} \\
D'_{2} &= -e \psi'_{2}, \quad D'_{1} = -e \psi'_{1}
\end{align*}
$$

### 2.2. The boundary conditions

For the unelectroded and traction-free surfaces, $T_{23} = 0, T'_{23} = 0$ and $D_2 = 0, D'_2 = 0$ at $x_2 = \pm h$, which are equal to:

$$
\begin{align*}
x_2 = \pm h: u_2 &= 0, \quad u'_{2} = 0, \quad \psi_{2} = 0, \quad \psi'_{2} = 0
\end{align*}
$$

For the imperfectly bonded interfaces at $x_1 = \pm a$, we adopt the spring-type relation [8], which requires:

$$
\begin{align*}
x_1 = \pm a: \quad T_{13} &= T'_{13} = K(u' - u) \\
D_{1} &= D'_{1} = \Gamma (\varphi' - \varphi)
\end{align*}
$$

where $K (N m^{-3})$ is the effective interface elastic stiffness parameter and $\Gamma (C V m^{-2})$ is the electrical imperfection parameter, which simultaneously describe how well the two materials are bonded.

When $K = 0$ and $\Gamma = 0$, the three portions lose their mechanical and electrical interaction. When $K = \infty$ and $\Gamma \neq \infty$, we consider the electrical imperfection only. The circumstance of $\Gamma = \infty$ and $K \neq \infty$ is the only consideration of the mechanical imperfection, which is the same as the shear-lag model [22–25]. The case of $K = \infty$ and $\Gamma = \infty$ is for the perfect interface with continuous displacement and electrical function across the interface.

We assume the two interfaces at $x_1 = \pm a$ have the same characteristics, i.e., they have the same effective interface elastic stiffness $K$ and the same electrical imperfection parameter $\Gamma$ simultaneously. As we know, this is impossible in practice, but it is helpful to investigate and understand the effect of the imperfect interfaces on the characteristics of the thickness–twist mode waves. Besides, the displacement and the electric potential are finite, which requires:

$$
|x_1| \to \infty: u' \to 0, \quad \varphi' \to 0
$$

### 3. Propagating wave solutions

It can be verified that solutions to Eqs. (2) and (4) can be classified into waves symmetric and anti-symmetric in the $x_1$ direction [5,7,8]. Here we only investigate the waves which are symmetric in the $x_1$ direction. So for the central portion, we have [9–11]

$$
\begin{align*}
\begin{cases}
\mathbf{u} = A_1 \cos(\xi x_1) \cos(\omega t) & \text{exp}(i\omega t) \\
\psi = B_1 \cosh(\xi x_1) \cos(\omega t) & \text{exp}(i\omega t)
\end{cases}
\end{align*}
$$

where $A_1$ and $B_1$ are undetermined constants, $\xi_1$ and $\xi_2$ are wave numbers in the $x_1$ and $x_2$ directions, $\omega = \sqrt{m(m = 0, 2, 4, \ldots)}$ is the wave frequency, and $f' = -1$. In particular, $m = 0$ is called face-shear wave mode, which will not be considered in the following.

Eq. (9) has satisfied with Eq. (6) and the second equation in Eq. (2). Inserting Eq. (9) into the first equation in Eq. (2), we have:

$$
\xi_1 = \sqrt{\frac{\rho \omega^2}{C_0^2} - \xi_2^2} = \frac{\rho}{C_0} \sqrt{\omega^2 - \frac{(m \pi)^2 C_0^2}{2h^2}} = \frac{1}{v} \sqrt{\omega^2 - \omega_m^2}
$$

where $v_1 = \sqrt{C/\rho}$ is the bulk shear wave velocity of the piezoelectric material occupying $x_1 < |a|$ and $\omega_m = (m \pi) v_T$ is the corresponding cut-off frequency of thickness–twist waves.

Similarly, for the modes of the outer portions [9–11]

$$
\begin{align*}
\begin{cases}
\mathbf{u}' = \begin{cases}
A'_1 \exp(-\xi'_1 (x_1 - a)) \cos(\omega t) & x_1 > a \\
A'_1 \exp(\xi'_1 (x_1 + a)) \cos(\omega t) & x_1 < -a
\end{cases} \\
\psi' = \begin{cases}
B'_1 \exp(-\xi'_2 (x_1 - a)) \cos(\omega t) & x_1 > a \\
B'_1 \exp(\xi'_2 (x_1 + a)) \cos(\omega t) & x_1 < -a
\end{cases}
\end{cases}
\end{align*}
$$

where $A'_1$ and $B'_1$ are undetermined constants, $\xi'_1$ is the wave number in the $x_1$ direction, which satisfied

$$
\xi'_1 = \sqrt{\begin{align*}
\frac{\rho \omega^2}{C_0^2} - \xi'_2^2 = \frac{1}{v'_1} \sqrt{\omega^2 - \omega'_m^2}
\end{align*}
$$

Similarly, $v'_1 = \sqrt{C/\rho}$ is the bulk shear wave velocity of the outer piezoelectric material and $\omega'_m = (m \pi) v'_T$ is the corresponding cut-off frequency.

Substituting Eq. (9) into Eq. (3) and inserting Eq. (11) into Eq. (5) respectively, $T_{13}, D_{1}, T_{13}$ and $D_{1}$ can be obtained. According to the boundary conditions Eq. (7), we can get:

$$
\begin{align*}
\begin{cases}
\mathbf{e} A' \xi'_1 - e B'_1 \xi'_2 = K [A'_1 - A_1 \cos(\xi_1 a)] \\
-e A_1 \sin(\xi_1 a) + e B_1 \sinh(\xi_2 a) = -e A' \xi'_1 - e B'_1 \xi'_2 \\
e B'_1 \xi'_2 = \Gamma [B'_1 + \frac{e A'_1}{2} - B_1 \cosh(\xi_2 a) - \xi_1 A_1 \cos(\xi_1 a)] \\
-e B_1 \sinh(\xi_2 a) = e B'_1 \xi'_2
\end{cases}
\end{align*}
$$

Fig. 1. An inhomogeneous transversely piezoelectric plate that the central portion is different from the rest portions with imperfectly bonded interfaces.
Eq. (13) is a four linear, homogeneous equation for $A_1$, $B_1$, $A'_1$ and $B'_1$. For nontrivial solutions, the determinant of the coefficient matrix has to vanish, which yields the frequency equation

$$M = M_{\text{perfect}} + M_K + M_F + M_{KR} = 0 \quad (14)$$

where

$$M_{\text{perfect}} = \left[ e \xi_1 - c \xi_1 \tan(\xi_1 a) \right] [e + c \tanh(\xi_2 a)]$$

and

$$M_K = \frac{1}{K} \left\{ \frac{\xi_1}{c^2} \left[ e^2 \xi_1 - c^2 \xi_2 \tan(\xi_1 a) \right] + e \xi_2 \tanh(\xi_2 a) \left[ \frac{e^2 \xi_1}{c^2} - \frac{c^2 \xi_2}{e^2} \xi_1 \tan(\xi_1 a) \right] \right\}$$

and

$$M_F = \frac{1}{K} \left\{ e \xi_2 \tanh(\xi_2 a) [c \xi_1 \tan(\xi_1 a) - c \xi'_1] \right\}.$$

$$M_{KR} = \frac{e \xi_2 \tanh(\xi_2 a) \xi_1 \tanh(\xi_2 a)}{K}$$

If we consider the electrical imperfection only, i.e., $\Gamma \neq 0$ and $K = \infty$, so $M_K = M_{KR} = 0$. Eq. (14) can be abbreviated as the form

$$M = M_{\text{perfect}} + M_F = 0 \quad (16)$$

Similarly, if we consider the mechanical imperfection only, i.e., $K = \neq 0$ and $\Gamma = \infty$, so $M_F = M_{KR} = 0$. Eq. (14) can be abbreviated as the form

$$M = M_{\text{perfect}} + M_K = 0 \quad (17)$$

which is the outcome by the shear-lag model [22–25]. For the perfect interfaces, i.e., $K = \infty$ and $\Gamma = \infty$, Eq. (14) can be written as

$$M_{\text{perfect}} = 0 \quad (18)$$

which is the same as the work by Yang et al. [9].

4. Numerical results

We choose the trapped mode for consideration, i.e., $\omega_n < \omega < \omega_{m}$ [8-10]. The central region and the outer regions are chosen to be PZT-5 and PZT-6B, respectively. The corresponding material parameters are list as Table 1 [27]. As a numerical example, the plate thickness is chosen to be $h = 1$ mm, and $m = 2$.

Contrasting the mechanical imperfection $M_K$ and the electrical imperfection $M_F$ in Eq. (15), we can find that $M_K$ has the dominant term of $c \xi_1 \xi'_1$ which has order of the product of $c$ and $\xi'$, while $M_F$ has the dominant term of $(c \xi_1 \tan(\xi_1 a) - c \xi'_1)$. Generally speaking, $c$ and $\xi'$ have the order of 10^10 as Table 1 depicted. Hence, if the effective interface elastic stiffness $K$ equals to the electrical imperfection parameter $\Gamma$, the value of $M_K$ will be much bigger than that of $M_F$. In order to prove the conclusion, we choose $K = \Gamma = 1 \times 10^{16}$ to calculate $M_K$ and $M_F$. The absolute values of $M_K$, $M_F$, and $M_{KR}$ are list as Table 2, which shows that the effect of mechanical imperfection is more evident than that of the electrical imperfection.

### Table 1
The material parameters.

<table>
<thead>
<tr>
<th>Materials</th>
<th>$\rho$ (kg/m^3)</th>
<th>$\epsilon$ (10^10 N/m^2)</th>
<th>$\varepsilon$ (C/m^2)</th>
<th>$\zeta$ (10^-6 C/V m)</th>
</tr>
</thead>
<tbody>
<tr>
<td>PZT-6B</td>
<td>7550</td>
<td>3.55</td>
<td>4.6</td>
<td>0.360</td>
</tr>
<tr>
<td>PZT-5</td>
<td>7750</td>
<td>2.11</td>
<td>12.3</td>
<td>0.811</td>
</tr>
</tbody>
</table>

### Table 2
The absolute values of $M_K$, $M_F$, and $M_{KR}$.

<table>
<thead>
<tr>
<th></th>
<th>The first mode</th>
<th>The third mode</th>
<th>The fifth mode</th>
</tr>
</thead>
<tbody>
<tr>
<td>$M_K$</td>
<td>$1.5415 \times 10^3$</td>
<td>$1.2136 \times 10^3$</td>
<td>$0.5618 \times 10^3$</td>
</tr>
<tr>
<td>$M_F$</td>
<td>$5.3950 \times 10^{-18}$</td>
<td>$5.0565 \times 10^{-18}$</td>
<td>$4.5370 \times 10^{-18}$</td>
</tr>
<tr>
<td>$M_{KR}$</td>
<td>$9.4603 \times 10^{-19}$</td>
<td>$7.2184 \times 10^{-19}$</td>
<td>$2.9289 \times 10^{-19}$</td>
</tr>
</tbody>
</table>

Fig. 2. The frequency $\omega$ and the frequency shift $\Delta \omega$ of the first mode as a function with the ratio $a/h$. (a) The frequency $\omega$. (b) The frequency shift $\Delta \omega$.  

Fig. 3. The frequency change $\Delta \omega$ as a function with $\gamma$. 

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F. Jin, P. Li / Ultrasonics 52 (2012) 33–38
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According to Table 2, we only consider the mechanical imperfection in the following, i.e., \(\Gamma = \infty\) and \(K \neq 0\). Assuming a non-dimensional number \(\gamma = \frac{c}{\zeta_2}/K\), so Eq. (14) can be written as the form

\[
\left[\frac{c'\zeta_1 - \zeta_1\tan(\zeta_1\alpha)}{c' + \tan(\zeta_2\alpha)} - \frac{\epsilon - \epsilon'}{\epsilon'}\right] \tanh(\zeta_2\alpha) \\
= \gamma \left\{ \frac{\zeta_1 c'\zeta_1\tan(\zeta_1\alpha)}{c' + \tan(\zeta_2\alpha)} \right\} \\
+ \frac{\epsilon'\tan(\zeta_2\alpha)}{c} \left[ \frac{\epsilon'}{\epsilon'} - \frac{\epsilon^2}{\epsilon^2} \frac{c}{c} \right] \tan(\zeta_1\alpha) \right\} (19)
\]

where \(\gamma = 0\), i.e., \(K = \infty\) is related to the perfect interfaces. The frequency shift can be defined as \(\Delta \omega = \omega - \omega_0\), where \(\omega\) is the frequency of the plate when the interfaces are imperfect, and \(\omega_0\) represents the frequency of the plate with the perfect interfaces. Fig. 2 is the frequency \(\omega\) and the frequency shift \(\Delta \omega\) of the first mode as the function with the ratio \(\alpha/h\).

Owing to the relation \(\omega_m < \omega_0\), the frequency of the first mode decreases with the increasing \(\alpha/h\), this can be seen from Fig. 2a. On the other hand, the frequencies will decrease if the interfaces are imperfectly bonded, which is because the imperfect interfaces reduce the stiffness of the plate. The two points illustrate the validity of the phase velocity equations obtained in our research work. When the ratio \(\alpha/h\) is small, the imperfect interfaces make a great impact on the frequencies of the plate, and with the ratio \(\alpha/h\) increasing, this kind of effect falls off, which can be seen from Fig. 2b. The frequencies of the higher modes have the
same tendency with the increasing ratio $a/h$, which are not depicted here. In the following discussion, we choose $a/h = 10$.

The frequency shift $\Delta \omega$ as a function with $\gamma$. From Fig. 3, we can conclude that the frequency shift $\Delta \omega = 0$ if the interfaces are perfect, i.e., $\gamma = 0$ or $K = \infty$, which also provides that our computation results are correct. Compared with the higher order modes, the first mode has a relatively smaller frequency change. The relationship between the frequency shift $\Delta \omega$ and the non-dimensional number $\gamma$ is linear, which can be explained by Chen et al. This relationship can be used to provide the foundation for a new experimental procedure for measuring the level of the interface bonding.

In order to deal with the imperfect interface, the spring-type relation can be applied, in which the interface can be treated as a layer that geometrically has a zero thickness but the tangential displacement is allowed to be different from both sides of the interface, so the discontinuous displacement can be seen at the imperfect interfaces, which can be proved by Fig. 4. Whether the interface is imperfect or not, the amplitude of the displacement component decays rapidly along the $x_1$ direction when the frequency of the plate $\omega$ satisfies $\omega_0 < \omega < \omega_m$. In the region $|x_1| > 0.02$ m, the displacement almost equals to zero, which means we cannot receive the thickness-twist waves. This is related to the energy-trapping phenomenon of the thickness-twist modes [7–11], in which the vibration is confined to the central portion of the plate and essentially, there is almost no vibration in the rest of the plate. So the plate can meet practical needs, such as wiring and mounting, in which the vibration of the outer portion cannot affect the central portion. On the other hand, the displacement in the case of imperfectly bonding is a little bit smaller than that in the case of perfectly bonding because the imperfectly bonding also absorbs some energy of the waves when they propagate through it. The displacement components of the higher modes have the similar tendency along the $x_1$ direction, which are not discussed here.

Similar with $\Delta \omega$, we can also define $\delta T_{13}$ as the stress change.

Figs. 5–7 are the stress component $T_{13}$ or $T'_{13}$ and the stress change $\delta T_{13}$ along the $x_1$ direction when $A_1 = 10^{-4}$. The energy-trapping phenomenon of the thickness-twist modes also can be seen owning to the frequency $\omega$ we adopted satisfies $\omega_0 < \omega < \omega_m$, and the stress component $T_{13}$ or $T'_{13}$ and the stress change $\delta T_{13}$ all anti-symmetric about $x_1 = 0$, which is because of the symmetric mode of the displacement component and the electrical potential function we adopted in Eqs. (9) and (11). Considering the imperfect interfaces, the stress component changes more evidently in the central portion $x_1 < |a|$ than in the outer portions $x_1 > |a|$, especially the stress $T_{13}$ or $T'_{13}$ changes most severely at the imperfect interfaces, which can be seen from Figs. 5–7.

5. Conclusions

The effect of the imperfectly bonded interfaces about the thickness-twist mode in an inhomogeneous piezoelectric plate in which the central portion is different from the rest portions is analyzed with the spring-type relation, which simultaneously takes the mechanical imperfection and the electrical imperfection into account. Results show that the effect of mechanical imperfection is more evident than that of the electrical imperfection. The linear relationship between the frequency shift $\Delta \omega$ and the non-dimensional number $\gamma$ can be used to measure the level of the interface bonding. The results theoretically can be used in the design of wave propagation in the piezoelectric coupled structures with an imperfect interface.

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